

PHASE CONTROL THYRISTORS

- Junction Size: Square 230 mils
- Wafer Size: 4"
- V_{RRM} Class: 600 and 1200 V
- Passivation Process: Glassivated MESA
- Reference IR Packaged Part: n. a.

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V_{TM} Maximum On-state Voltage	1.3 V	$T_J = 25^\circ\text{C}$, $I_T = 25\text{ A}$
V_{RRM} Reverse Breakdown Voltage	600 and 1200 V	$T_J = 25^\circ\text{C}$, $I_{RRM} = 100\text{ }\mu\text{A}$ (1)
I_{GT} Max. Required DC Gate Current to Trigger	60 mA	$T_J = 25^\circ\text{C}$, anode supply = 6 V, resistive load
V_{GT} Max. Required DC Gate Voltage to Trigger	1.9 V	$T_J = 25^\circ\text{C}$, anode supply = 6 V, resistive load
I_H Holding Current Range	5 to 150 mA	Anode supply = 6 V, resistive load
I_L Maximum Latching Current	400 mA	Anode supply = 6 V, resistive load

(1) Nitrogen flow on die edge.

Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Chip Dimensions	230 x 230 mils (see drawing)
Wafer Diameter	100 mm, with std. < 100 > flat
Wafer Thickness	370 $\mu\text{m} \pm 10\text{ }\mu\text{m}$
Maximum Width of Sawing Line	130 μm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

Bulletin 10205J 07/98

Wafer Layout

